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SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT

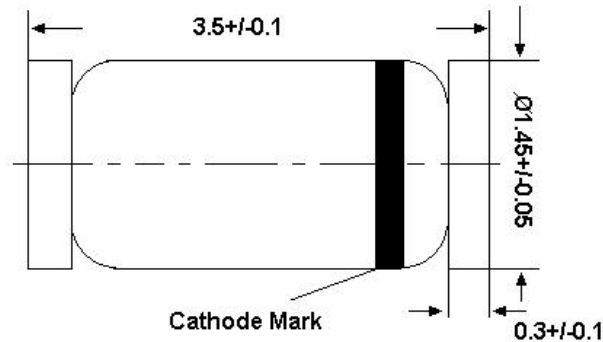


PLED

LLDB3/LLDB4

Product specification

These diacs are intended for use in thyristor phase control, circuits for lamp-dimming, universal-motor speed controls, and heat controls.



Glass case MiniMELF
Dimensions in mm
LL-34

REEL SPECIFICATION

P/N	PKG	QTY
LLDB3/LLDB4	LL-34	2500

Absolute Maximum Ratings (T_a = 25°C)

Parameter	Symbol	Value	Unit
Power Dissipation (T _a = 65 °C)	P _{tot}	150	mW
Repetitive Peak On-state Current (t _p = 20 μs, f = 100 Hz)	I _{TRM}	2	A
Operating Junction and Storage Temperature Range	T _j , T _{stg}	- 40 to + 125	°C

Characteristics at T_a = 25°C)

Parameter	Symbol	Min.	Max.	Unit
Breakover Voltage at C = 22 nF, see diagram 1	V _{BO}	28	36	V
		35	45	
Breakover Voltage Symmetry at C = 22 nF, see diagram 1	[+V _{BO} - -V _{BO}]	-	3	V
Dynamic Breakover Voltage at ΔI = [I _{BO} to I _F = 10 mA]	ΔV ±	5	-	V
Output Voltage See diagram 2	V _O	5	-	V
Breakover Current at C = 22 nF	I _{BO}	-	50	μA
Leakage Current at V _B = 0.5 V _{BO} max	I _B	-	10	μA
Rise Time See diagram 3	t _r	-	2	μs

Diagram 1: Current-voltage characteristics

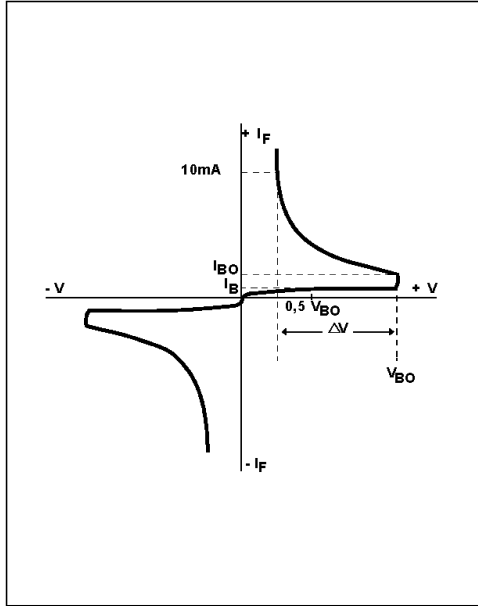


Diagram 2: Test circuit for output voltage

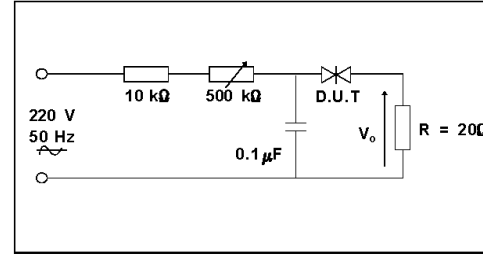


Diagram 3: Test circuit see diagram 2. Adjust R for $I_p = 0.5A$

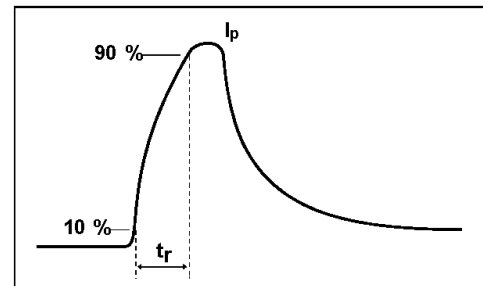


Fig. 1: Power dissipation versus ambient temperature (maximum values)

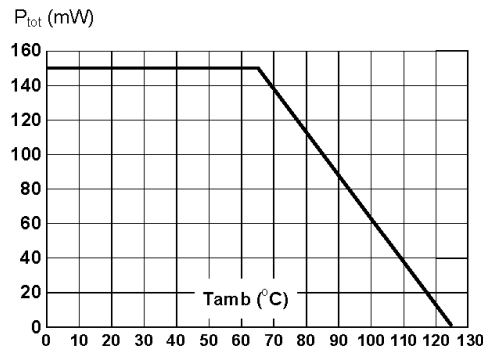


Fig. 2: Relative variation of V_{BO} versus junction temperature (typical values)

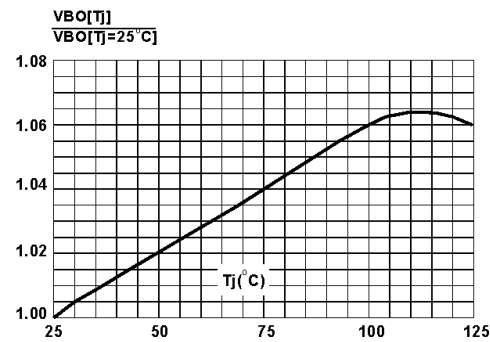
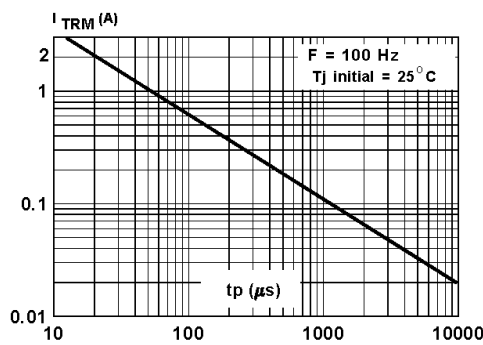


Fig. 3: Peak pulse current versus pulse duration (maximum values)



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